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Ambipolar Characteristics Based on Complementary MoS₂ and WSe₂ Field-Effect Transistors

박지민, 손장엽, 박상규, 전대영^a

Jimin Park, Jangyup Son, Sang Kyu Park, Dae-Young Jeon^a

한국과학기술연구원

Abstract:

Recently, semiconducting two-dimensional (2D) transition metal dichalcogenide (TMD) material-based field-effect transistors (FETs) were studied actively to overcome the short channel effects (SCEs), which are fundamental issues in scaling of logic transistors for the continuation of Moore's law [1,2].

In this work, complementary MoS₂ and WSe₂ FETs were fabricated by selective patterning with alignment technique. WSe₂ and MoS₂ channels were placed on highly doped-Si/SiO₂ substrate using mechanical exfoliation and dry transfer method to utilize p- and n-type channel, respectively. Then, we successfully obtained ambipolar transfer curves from the complementary MoS₂ and WSe₂ FETs. In addition, I_d-V_d and I_d-V_g characteristics of each polarity transistor were analyzed to verify the ambipolar operation and several advantages of the complementary FETs. This work can provide useful information of structure design to investigate proper electrical operation of 2D material-based ambipolar transistors.

Keywords

Semiconducting 2D TMDs materials, MoS₂ and WSe₂ FETs, Complementary FETs, Ambipolar transistors

참고문헌

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a. Corresponding Author ; dyjeon@kist.re.kr
